

WHAT IS CLAIMED IS:

1. A method for burying a resist comprising the steps of:
forming an interlayer film on a substrate;
5 forming an opening in said interlayer film;
coating a resist film onto said interlayer film including
said opening; and
patterning said resist film substantially in the same form
as said opening, thereby burying said resist film in the inside
10 of said opening.
2. A method for burying a resist comprising the steps of:
forming an interlayer film on a substrate;
forming an opening in said interlayer film;
15 forming another film on said interlayer film including said
opening;
coating a resist film on said another film; and
patterning said resist film substantially in the same form
as said opening, thereby burying said resist film in the inside
20 of said opening.
3. The method for burying a resist according to claim 1,
wherein said resist is made of a positive resist and said resist
is patterned by use of a photomask having a light-shielding
25 portion whose region is smaller than said opening.
4. The method for burying a resist according to claim 2,
wherein said resist is made of a positive resist and said resist
is patterned by use of a photomask having a light-shielding
30 portion whose region is smaller than said opening.
5. The method for burying a resist according to claim 1,

wherein said resist is made of a negative resist and said resist is patterned by use of a photomask having a light-transmitting portion whose region is smaller than said opening.

5 6. The method for burying a resist according to claim 2, wherein said resist is made of a negative resist and said resist is patterned by use of a photomask having a light-transmitting portion whose region is smaller than said opening.

10 7. A method for manufacturing a semiconductor device comprising the steps of:

forming an interlayer film on a substrate;
forming an opening in said interlayer film;
coating a resist film on said interlayer film including

15 said opening;

 patterning said resist film substantially in the same form as said opening, thereby burying said resist film in the inside of said opening; and

 etching said interlayer film while masking a bottom portion
20 of said opening with said resist film buried in said opening.

 8. A method for manufacturing a semiconductor device comprising the steps of:

forming an interlayer film on a substrate;
25 forming an opening in said interlayer film;
coating another film on said interlayer film including said opening;

coating a resist film on said another film; and

 patterning said resist film substantially in the same form
30 as said opening, thereby burying said resist film in the inside of said opening; and

 etching said another film while masking a bottom portion of

said opening with said resist film buried in said opening.